

Enhancement Mode MOSFET Arrays (Includes Low Threshold MOSFETs)

N-Channel

Device	Channels	BV _{DSS} min (V)	R _{DS(ON)} max (Ω)	C _{ISS} typical (pF)	V _{GS(th)} max (V)	Package Options	Application Notes
TD9944	2	240	6.0	65	2.0	8-Lead SOIC (TG)	-
TN0604	4	40	1.0	140	1.6	20-Lead SOIC (WG)	AN-D09

P-Channel

Device	Channels	BV _{DSS} min (V)	R _{DS(ON)} max (Ω)	Package Options	Application Notes
TP0604	4	-40	2.0	20-Lead SOIC (WG)	AN-D09

Complementary MOSFET Arrays

Device	BV _{DSS} /BV _{DGS}		R _{DS(ON)} Max		V _{GS(th)} max (V)	Package Options	Application Notes	Notes
	N-Channel (V)	P-Channel (V)	N-Channel (Ω)	P-Channel (Ω)				
TC1550	500	-500	60	125	4.0	8-Lead SOIC (TG)	-	1
TC2320	200	-200	7.0	12	2.0	8-Lead SOIC (TG)	-	1
TC6215	150	-150	4.0	7.0	2.0	8-Lead SOIC (TG)	-	1
TC6320	200	-200	7.0	8.0	2.0	8-Lead QFN (K6)	AN-H53	1
						8-Lead SOIC (TG)		
TC7320	200	-200	20	20	0.4 (typ)	32-Lead LQFP (FG)	AN-H53	2

Notes:

1. N & P-channel pair.
2. Six N & P-channel pairs.

Insulated Gate Bipolar Transistors (IGBT)

Device	BV _(continuous) (V)	IC _(continuous) (A)	IC _(pulsed) (A)	Package Option
GN2470	700	1.0	3.5	3-Lead TO-252 (K4)